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FORM PTO-1449 (modified)
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M#

Client Ref

273686

FOO-219-US-DIV-3

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Applicant: MANABE et al.

Div. of Appln. No.: 09/417,778

Filing Date: October 14, 1999

Examiner: Minh Loan Tran Group Art Unit: 2811

Date: OCTOBER 2, 2000

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Examiner: Minh Loan Tran

Group Art Unit: 2811

Date: October 2, 2000

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| | QR 02-081484 | 03/1990 | Japan | Manabe | | | | x | | x |
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Applicant: MANABE et al.

Div of Appln. No.: 09/417,778

Filing Date: October 14, 1999

Examiner: Minh Loan Tran Group Art Unit: 2811

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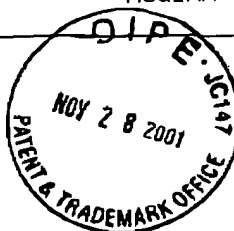
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Applicant: MANAB TECHNOLOGY CENTER 2800

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Filing Date: October 2, 2000

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Examiner: S. Mulpuri

Group Art Unit: 2812

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